



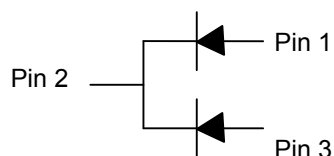
**SINLOON®**  
POWER SEMICONDUCTORS

## SB10150FCT

10A High Voltage Dual Schottky Barrier Rectifier

### FEATURE:

- ◆ Schottky Barrier Chip.
- ◆ Guard Ring for Transient Protection.
- ◆ Low Forward Voltage Drop.
- ◆ Low Reverse Leakage Current.
- ◆ High Surge Current Capability.
- ◆ Plastic Material has UL Flammability Classification 94V-0



### MECHANICAL DATA

- ◆ Cass: ITO-220, Full Molded Plastic.
- ◆ Terminals: Plated Leads Solder able per MIL-STD-202 Method 208.
- ◆ Polarity: See Diagram.
- ◆ Weight: 2.24 grams (approx).
- ◆ Mounting: Position : Any.
- ◆ Mounting Torque: 11.5 cm·kg (10 in·lbs) Max.
- ◆ Lead Free: For RoHS/ Lead Free Version.
- ◆ Add "LF" Suffix to Part Number, See Data.

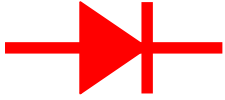
ITO-220		
Dim.	Min.	Max.
A	14.60	15.40
B	9.70	10.30
C	2.55	2.85
D	3.560	4.160
E	13.00	13.80
F	0.30	0.90
G	Φ3.00	Φ3.50
H	6.300	6.900
I	4.200	4.800
J	2.500	2.900
K	0.360	0.800
L	2.900	3.300
P	2.290	2.790

All Dimensions in mm

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS @TA = 25°C unless otherwise specified

Characteristic	Symbol	SB10150FCT	Unit	
Peak Repetitive Reverse Voltage	VRRM	150	V	
Working Peak Reverse Voltage	VRWM			
DC Blocking Voltage	VR			
RMS Reverse Voltage	VR(RMS)	105	V	
Average Rectified Output Current @Tc=105°C	IO	10.0	A	
Non-Repetitive Peak Forward Surtge Current	IFSM	150	A	
8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)				
Forward Voltage	@IF=8.0A	VFM	0.92	V
Peak Reverse Current	@TA=25°C	IRM	0.5	uA
At Rated DC Blocking Voltage	@TA=125°C		50	
Reverse Recovery Time (Note 2)		Cj	700	pF
Storage Temperature Range	Tj, TSTG		-55 to +150	°C

**Note:** 1). Measure at 1.0 MHz and Applied reverse voltage of 4.0V.DC.



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## DATA CURVE

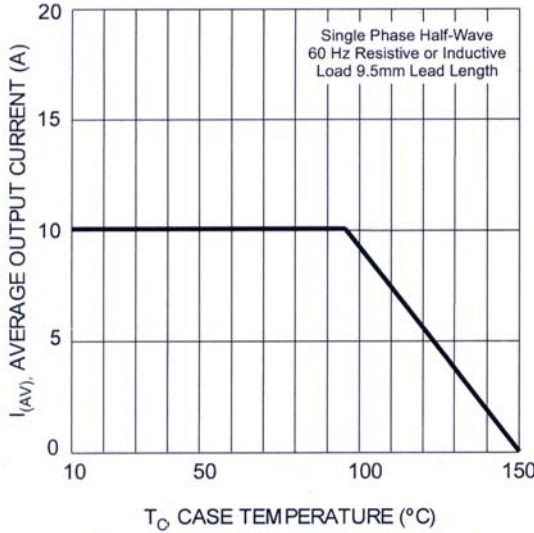


Fig. 1 Forward Current Derating Curve

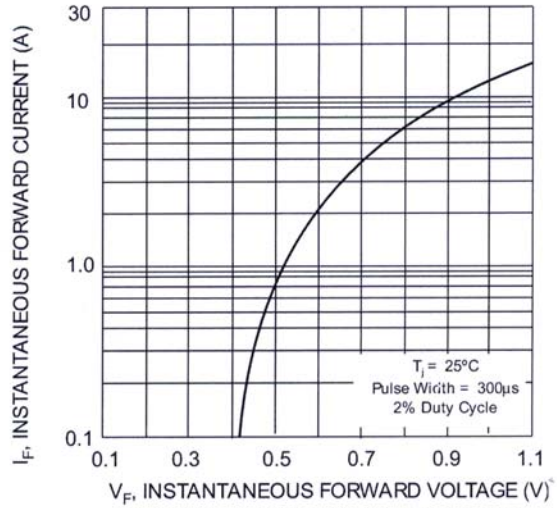


Fig. 2 Typical Forward Voltage Characteristics

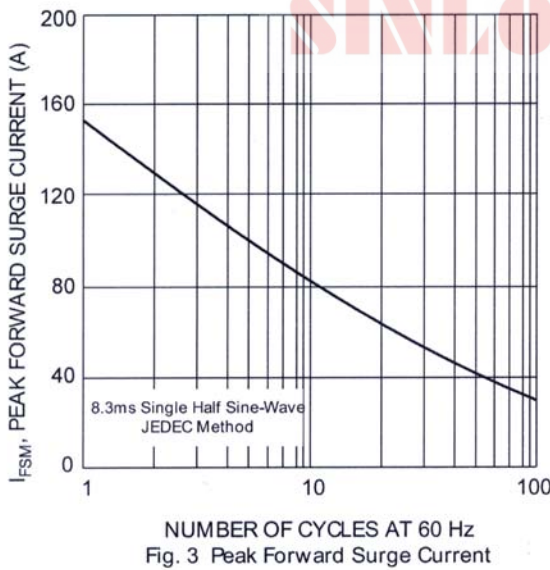


Fig. 3 Peak Forward Surge Current

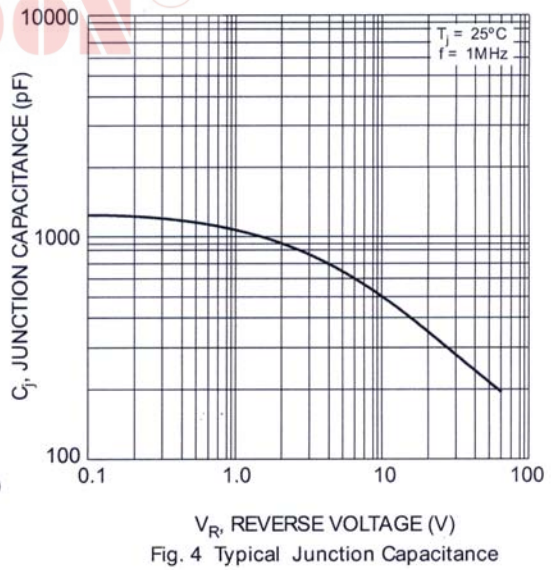


Fig. 4 Typical Junction Capacitance



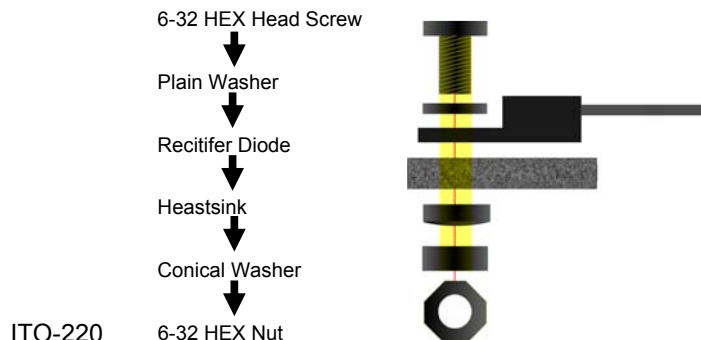
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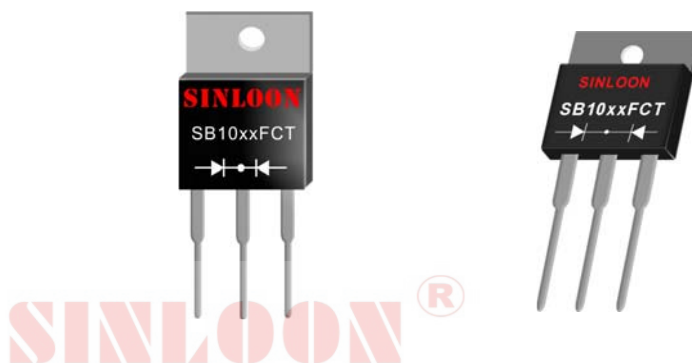
### RECOMMENDED SCREW MOUNTING ARRANGEMENT

- ◆ The full molded plastic package affords a major reduction of hardware as compared to a standard TO-220 package. However, precautions should be made in mounting procedure.
- ◆ A conical washer should be used to apply proper force to the device, Screw should not be tightened with any type of air-forced torque or equipment that may cause crack on device package.
- ◆ A layer of thermal grease or thermal pad in the interface will be considerably helpful for heat dissipation



### MARKING INFORMATION

XXX	=	Marking Logo
SB10150CT	=	Device Number
XX	=	150FCT
Polarity	=	As Marked on body.



### PACKAGING INFORMATION

Tube Size	Quantity	Inner Box Size	Quantity	Carton Size	Quantity	Approx. Gross Weight
LxWXH (mm)	(Pcs)	LxWXH (mm)	(Pcs)	LxWXH (mm)	(Pcs)	(Kg)
525x31x6	50	555x145x95	2000	572x306x218	8000	19

### PACKAGING INFORMATION

Product No.	Package Type	Carton Quantity
SB10150FCT	ITO-220	50 Units/Tube

- 1). Ordering Information  
Shipping quantity given is for minimum packing quantity only, For minimum. Order quantity, please consult the Sales Department.
- 2). To Order RoHS ./ Lead Free version (with Lead Free finish) . add "LF" suffix. To part uimper above. For example.  
SB10150FCT-LF